

Karol Frohlich

List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/6837279/publications.pdf>

Version: 2024-02-01

166
papers

1,982
citations

257357

24
h-index

377752

34
g-index

166
all docs

166
docs citations

166
times ranked

2058
citing authors

#	ARTICLE	IF	CITATIONS
1	Additive Manufacturing in Atomic Layer Processing Mode. Small Methods, 2022, 6, e2101546.	4.6	6
2	Doping efficiency and electron transport in Al-doped ZnO films grown by atomic layer deposition. Journal of Applied Physics, 2021, 130, 035106.	1.1	5
3	Si-Based Metal-Insulator-Semiconductor Structures with RuO ₂ (IrO ₂) Films for Photoelectrochemical Water Oxidation. ACS Applied Energy Materials, 2021, 4, 11162-11172.	2.5	7
4	Growth of In- and Ga ₂ O ₃ epitaxial layers on sapphire substrates using liquid-injection MOCVD. Semiconductor Science and Technology, 2020, 35, 115002.	1.0	13
5	Growth of lithium hydride thin films from solutions: Towards solution atomic layer deposition of lithiated films. Beilstein Journal of Nanotechnology, 2019, 10, 1443-1451.	1.5	2
6	SPICE model for the current-voltage characteristic of resistive switching devices including the snapback effect. Microelectronic Engineering, 2019, 215, 110998.	1.1	6
7	Compact Modeling of Complementary Resistive Switching Devices Using Memdiodes. IEEE Transactions on Electron Devices, 2019, 66, 2831-2836.	1.6	11
8	Functionalized graphene transistor for ultrasensitive detection of carbon quantum dots. Journal of Applied Physics, 2019, 126, 214303.	1.1	3
9	Operando diagnostic detection of interfacial oxygen "breathing" of resistive random access memory by bulk-sensitive hard X-ray photoelectron spectroscopy. Materials Research Letters, 2019, 7, 117-123.	4.1	19
10	Application of Atomic Layer Deposition for Fabrication of Solar Cells. ECS Meeting Abstracts, 2019, , .	0.0	0
11	Silicon based MIS photoanode for water oxidation: A comparison of RuO ₂ and Ni Schottky contacts. Applied Surface Science, 2018, 461, 48-53.	3.1	18
12	MIS Structures with RuO ₂ Schottky Contact for Photoelectrochemical Water Splitting. , 2018, , .		0
13	Three dimensional integration of ReRAMs. , 2018, , .		0
14	Hafnium oxide and tantalum oxide based resistive switching structures for realization of minimum and maximum functions. Journal of Applied Physics, 2018, 124, .	1.1	8
15	Characterization of interface states in AlGaIn/GaN metal-oxide-semiconductor heterostructure field-effect transistors with HfO ₂ gate dielectric grown by atomic layer deposition. Applied Surface Science, 2018, 461, 255-259.	3.1	11
16	Performance of HfO _x - and TaO _x -based Resistive Switching Structures for Realization of Minimum and Maximum Functions. MRS Advances, 2018, 3, 3427-3432.	0.5	2
17	Atomic layer deposition and properties of mixed Ta ₂ O ₅ and ZrO ₂ films. AIP Advances, 2017, 7, .	0.6	26
18	Effect of oxygen concentration and metal electrode on the resistive switching in MIM capacitors with transition metal oxides. Journal of Physics: Conference Series, 2017, 794, 012016.	0.3	3

#	ARTICLE	IF	CITATIONS
19	Influence of oxygen-plasma treatment on AlGaIn/GaN metal-oxide-semiconductor heterostructure field-effect transistors with HfO ₂ by atomic layer deposition: leakage current and density of states reduction. Semiconductor Science and Technology, 2017, 32, 045018.	1.0	18
20	Low-temperature atomic layer deposition-grown Al ₂ O ₃ gate dielectric for GaN/AlGaIn/GaN MOS HEMTs: Impact of deposition conditions on interface state density. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2017, 35, .	0.6	21
21	Annealing, temperature, and bias-induced threshold voltage instabilities in integrated E/D-mode InAlN/GaN MOS HEMTs. Applied Physics Letters, 2017, 111, .	1.5	10
22	Investigation of $\tilde{\epsilon}$ surface donors TM in Al ₂ O ₃ /AlGaIn/GaN metal-oxide-semiconductor heterostructures: Correlation of electrical, structural, and chemical properties. Applied Surface Science, 2017, 426, 656-661.	3.1	27
23	Interface engineered HfO ₂ -based 3D vertical ReRAM. Journal Physics D: Applied Physics, 2016, 49, 215102.	1.3	26
24	Threshold voltage instabilities in AlGaIn/GaN MOS-HEMTs with ALD-grown Al ₂ O ₃ gate dielectrics: Relation to distribution of oxide/semiconductor interface state density. , 2016, , .		0
25	Electrical characterisation of MIS photoanodes annealed under different conditions for solar fuel generation. , 2016, , .		2
26	Temperature-dependent of sub-threshold slope of AlGaIn/GaN MOSHFETs with HfO ₂ gate oxide prepared by ALD. , 2016, , .		0
27	Effect of HCl pretreatment on the oxide/semiconductor interface state density in AlGaIn/GaN MOS-HEMT structures with MOCVD grown Al ₂ O ₃ gate dielectric. , 2016, , .		0
28	The influence of ozone pre-treatment in HfO ₂ -based resistive switching memory structures. , 2016, , .		0
29	DC and pulsed IV characterisation of AlGaIn/GaN MOS-HEMT structures with Al ₂ O ₃ gate dielectric prepared by various techniques. , 2016, , .		0
30	3D resistive RAM cell design for high-density storage class memory—a review. Science China Information Sciences, 2016, 59, 1.	2.7	54
31	Modeling of the switching I-V characteristics in ultrathin (5 nm) atomic layer deposited HfO ₂ films using the logistic hysteron. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2015, 33, 01A102.	0.6	6
32	Resistive switching in nonplanar HfO ₂ -based structures with variable series resistance. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2015, 33, 01A108.	0.6	6
33	Self-aligned normally off metal-oxide-semiconductor n ⁺⁺ GaN/InAlN/GaN high electron mobility transistors. Physica Status Solidi (A) Applications and Materials Science, 2015, 212, 1086-1090.	0.8	23
34	On Passive Permutation Circuits. IEEE Journal on Emerging and Selected Topics in Circuits and Systems, 2015, 5, 173-182.	2.7	3
35	Model for the Current-Voltage Characteristic of Resistive Switches Based on Recursive Hysteretic Operators. IEEE Electron Device Letters, 2015, 36, 944-946.	2.2	4
36	Gate leakage reduction of AlGaIn/GaN MOS-HFETs with HfO ₂ prepared by ALD. , 2014, , .		0

#	ARTICLE	IF	CITATIONS
37	Frequency dependent capacitance of insulator GaN/AlGaN/GaN heterostructure. , 2014, , .		0
38	InGaAs/GaAs metal-oxide-semiconductor heterostructure field-effect transistors with oxygen-plasma oxide and Al ₂ O ₃ double-layer insulator. Applied Physics Letters, 2014, 105, 183504.	1.5	10
39	Influence of growth temperature on the structure and electrical properties of high-permittivity Ti ₂ O ₂ films in Ti ₄ Cl ₄ H ₂ O and Ti ₄ Cl ₄ O ₃ atomic-layer deposition processes. Physica Status Solidi (A) Applications and Materials Science, 2014, 211, 425-432.	0.8	14
40	Adjustment of threshold voltage in AlN/AlGaN/GaN high-electron mobility transistors by plasma oxidation and Al ₂ O ₃ atomic layer deposition overgrowth. Applied Physics Letters, 2014, 104, .	1.5	31
41	Resistive switching effects in Pt/HfO ₂ /TiN MIM structures and their dependence on bottom electrode interface engineering. , 2014, , .		0
42	Atomic layer deposition of high-quality Al ₂ O ₃ and Al-doped TiO ₂ thin films from hydrogen-free precursors. Thin Solid Films, 2014, 565, 19-24.	0.8	31
43	Nanoscale Characterization of TiO ₂ Films Grown by Atomic Layer Deposition on RuO ₂ Electrodes. ACS Applied Materials & Interfaces, 2014, 6, 2486-2492.	4.0	21
44	Resistive switching in TiO ₂ -based metal-insulator-metal structures with Al ₂ O ₃ barrier layer at the metal/dielectric interface. Thin Solid Films, 2014, 563, 10-14.	0.8	20
45	Resistive switching in HfO ₂ -based atomic layer deposition grown metal-insulator-metal structures. Applied Surface Science, 2014, 312, 112-116.	3.1	20
46	The influence of technology and switching parameters on resistive switching behavior of Pt/HfO ₂ /TiN MIM structures. Facta Universitatis - Series Electronics and Energetics, 2014, 27, 621-630.	0.6	3
47	Atomic Layer Deposition of Thin Oxide Films for Resistive Switching. ECS Transactions, 2013, 58, 163-170.	0.3	5
48	TiO ₂ -based structures for nanoscale memory applications. Materials Science in Semiconductor Processing, 2013, 16, 1186-1195.	1.9	24
49	Atomic layer deposition of rutile-phase TiO ₂ on RuO ₂ from TiCl ₄ and O ₃ : Growth of high-permittivity dielectrics with low leakage current. Journal of Crystal Growth, 2013, 382, 61-66.	0.7	17
50	Ni/Au-Al ₂ O ₃ gate stack prepared by low-temperature ALD and lift-off for MOS HEMTs. Microelectronic Engineering, 2013, 112, 204-207.	1.1	10
51	Schottky-barrier normally off GaN/InAlN/AlN/GaN HEMT with selectively etched access region. IEEE Electron Device Letters, 2013, 34, 432-434.	2.2	33
52	Impact of plasma treatment on electrical properties of TiO ₂ /RuO ₂ -based DRAM capacitor. Journal Physics D: Applied Physics, 2013, 46, 385304.	1.3	27
53	TiO ₂ -Based Metal-Insulator-Metal Structures for Future DRAM Storage Capacitors. ECS Transactions, 2013, 50, 79-87.	0.3	12
54	Properties of Al ₂ O ₃ thin films grown by atomic layer deposition. , 2012, , .		3

#	ARTICLE	IF	CITATIONS
55	Distribution of fixed oxide charge in MOS structures with ALD grown Al ₂ O ₃ studied by capacitance measurements. , 2012, , .		1
56	Atomic layer deposition of high-permittivity TiO ₂ dielectrics with low leakage current on RuO ₂ /TiCl ₄ -based processes. Semiconductor Science and Technology, 2012, 27, 074007.	1.0	17
57	Influence of processing and annealing steps on electrical properties of InAlN/GaN high electron mobility transistor with Al ₂ O ₃ gate insulation and passivation. Solid-State Electronics, 2012, 67, 74-78.	0.8	17
58	Electrical properties of InAlN/GaN high electron mobility transistor with Al ₂ O ₃ , ZrO ₂ , and GdScO ₃ gate dielectrics. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2011, 29, .	0.6	30
59	Analysis of leakage current mechanisms in RuO ₂ /TiO ₂ /RuO ₂ MIM structures. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2011, 29, 01AC08.	0.6	5
60	Trap-assisted tunnelling current in MIM structures. Open Physics, 2011, 9, .	0.8	2
61	Structural and dielectric properties of Ru-based gate/Hf-doped Ta ₂ O ₅ stacks. Applied Surface Science, 2011, 257, 7876-7880.	3.1	13
62	Electrical properties of TiO ₂ -based MIM capacitors deposited by TiCl ₄ and TTIP based atomic layer deposition processes. Microelectronic Engineering, 2011, 88, 1514-1516.	1.1	21
63	Post-deposition processing and oxygen content of TiO ₂ -based capacitors. Microelectronic Engineering, 2011, 88, 1525-1528.	1.1	9
64	Atomic layer deposition grown metal-insulator-metal capacitors with RuO ₂ electrodes and Al-doped rutile TiO ₂ dielectric layer. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2011, 29, 01AC09.	0.6	14
65	Low Equivalent Oxide Thickness TiO ₂ Based Capacitors for DRAM Application. ECS Transactions, 2011, 41, 73-77.	0.3	8
66	Gadolinium Scandate: Next Candidate for Alternative Gate Dielectric in CMOS Technology?. Journal of Electrical Engineering, 2011, 62, 54-56.	0.4	8
67	RuO ₂ /TiO ₂ based MIM capacitors for DRAM application. , 2010, , .		1
68	Proposal and Performance Analysis of Normally Off GaN/InAlN/AlN/GaN HEMTs With 1-nm-Thick InAlN Barrier. IEEE Transactions on Electron Devices, 2010, 57, 2144-2154.	1.6	31
69	Growth of RuO ₂ thin films by liquid injection atomic layer deposition. Thin Solid Films, 2010, 518, 4701-4704.	0.8	20
70	Optimization of the ohmic contact processing in InAlN//GaN high electron mobility transistors for lower temperature of annealing. Physica Status Solidi C: Current Topics in Solid State Physics, 2010, 7, 108-111.	0.8	6
71	High-permittivity metal-insulator-metal capacitors with TiO ₂ rutile dielectric and RuO ₂ bottom electrode. IOP Conference Series: Materials Science and Engineering, 2010, 8, 012024.	0.3	16
72	RF Performance of InAlN/GaN HFETs and MOSHFETs With TiO_2 dielectric and RuO_2 bottom electrode. up to 21 GHz. IEEE Electron Device Letters, 2010, 31, 180-182.	2.2	34

#	ARTICLE	IF	CITATIONS
73	Gate oxide thickness dependence of the leakage current mechanism in Ru/Ta ₂ O ₅ /SiON/Si structures. Semiconductor Science and Technology, 2010, 25, 075007.	1.0	7
74	Resistive switching in RuO ₂ /TiO ₂ /RuO ₂ MIM structures for non-volatile memory application. , 2010, , .		2
75	Characterization of high permittivity GdScO ₃ films prepared by liquid injection MOCVD. , 2010, , .		0
76	InAlN/GaN metal-oxide-semiconductor high electron mobility transistor with Al ₂ O ₃ insulating films grown by metal organic chemical vapor deposition using Ar and NH ₃ carrier gases. Journal of Vacuum Science & Technology B, 2009, 27, 218.	1.3	10
77	Interface States and Trapping Effects in Al ₂ O ₃ - and ZrO ₂ /InAlN/AlN/GaN Metal-Oxide Semiconductor Heterostructures. Japanese Journal of Applied Physics, 2009, 48, 090201.	0.8	14
78	Epitaxial growth of high- κ TiO ₂ rutile films on RuO ₂ electrodes. Journal of Vacuum Science & Technology B, 2009, 27, 266-270.	1.3	40
79	Thermal stability of GdScO ₃ and LaLuO ₃ films prepared by liquid injection MOCVD. Vacuum, 2009, 84, 170-173.	1.6	12
80	Thermally induced voltage shift in capacitance-voltage characteristics and its relation to oxide/semiconductor interface states in Ni/Al ₂ O ₃ /InAlN/GaN heterostructures. Semiconductor Science and Technology, 2009, 24, 035008.	1.0	39
81	Ultrathin InAlN/AlN Barrier HEMT With High Performance in Normally Off Operation. IEEE Electron Device Letters, 2009, 30, 1030-1032.	2.2	57
82	Current transport in MIM Structures. , 2009, , .		1
83	InAlN/GaN heterostructures for microwave power and beyond. , 2009, , .		4
84	Preparation of High Permittivity GdScO ₃ Films by Liquid Injection MOCVD. ECS Transactions, 2009, 25, 1061-1064.	0.3	5
85	Influence of GaN capping on performance of InAlN/AlN/GaN MOS-HEMT with Al ₂ O ₃ gate insulation grown by CVD. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 1956-1958.	0.8	10
86	Effect of Ti doping on Ta ₂ O ₅ stacks with Ru and Al gates. Applied Surface Science, 2008, 254, 5879-5885.	3.1	18
87	InAlN/GaN MOSHEMT with Al ₂ O ₃ insulating film. , 2008, , .		0
88	Electrical characterization of Ru-and RuO ₂ /Ta ₂ O ₅ gate stacks for nanoscale DRAM technology. , 2008, , .		0
89	Low equivalent oxide thickness metal/insulator/metal structures for DRAM application. , 2008, , .		0
90	Work function thermal stability of RuO ₂ -rich Ru-SiO ₂ p-channel metal-oxide-semiconductor field-effect transistor gate electrodes. Journal of Applied Physics, 2008, 103, 073702.	1.1	6

#	ARTICLE	IF	CITATIONS
91	Gate insulation and drain current saturation mechanism in InAlN ^x -GaN metal-oxide-semiconductor high-electron-mobility transistors. Applied Physics Letters, 2007, 91, .	1.5	71
92	Optimization and performance of Al ₂ O ₃ /GaN metal-oxide-semiconductor structures. Microelectronics Reliability, 2007, 47, 790-793.	0.9	15
93	Evidence of hafnia oxygen vacancy defects in MOCVD grown Hf _x Si _{1-x} O _y ultrathin gate dielectrics gated with Ru electrode. Microelectron Engineering, 2007, 84, 2366-2369.	1.1	5
94	Leakage characteristics of advanced MOS capacitors with hafnium silicate dielectric and Ru electrode. , 2006, , .		0
95	Energy Band Diagram of the Ru/Hf _{0.75} Si _{0.25} O _y /Si Gate Stack. , 2006, , .		0
96	Rapid thermal annealing and performance of Al ₂ O ₃ /GaN metal-oxide-semiconductor structures. , 2006, , .		0
97	Microstructure of HfO ₂ and Hf _x Si _{1-x} O _y Dielectric Films Prepared on Si for Advanced CMOS Application. , 2006, , .		2
98	Precise determination of metal effective work function and fixed oxide charge in MOS capacitors with high- ϵ_r dielectric. Materials Science in Semiconductor Processing, 2006, 9, 969-974.	1.9	24
99	Characterization of rare earth oxides based MOSFET gate stacks prepared by metal-organic chemical vapour deposition. Materials Science in Semiconductor Processing, 2006, 9, 1065-1072.	1.9	24
100	Electrically conductive SiC ^x (Nb,Ti) _{ss} (Nb,Ti) _{Css} cermet. Journal of the European Ceramic Society, 2006, 26, 1259-1266.	2.8	19
101	Electrical properties and thermal stability of MOCVD grown Ru gate electrodes for advanced CMOS technology. Microelectron Engineering, 2006, 83, 2412-2416.	1.1	5
102	Growth of Ru/RuO ₂ layers with atomic vapor deposition on plain wafers and into trench structures. Microelectron Engineering, 2006, 83, 2277-2281.	1.1	10
103	Phase stability of La _{0.5} Sr _{0.5} CoO _{3-x} films upon annealing in hydrogen atmosphere. Journal of Applied Physics, 2006, 100, 044501.	1.1	7
104	Thermal Stability of Ru Gate Electrode on HfSiO Dielectric. Materials Research Society Symposia Proceedings, 2006, 917, 1.	0.1	1
105	FIXED OXIDE CHARGE IN Ru-BASED CHEMICAL VAPOUR DEPOSITED HIGH- ϵ_r GATE STACKS. , 2006, , 277-286.		0
106	Growth of gadolinium oxide films for advanced MOS structure. Microelectron Engineering, 2005, 80, 154-157.	1.1	22
107	Complementarity of X-ray diffraction and RBS in thin film characterization. Vacuum, 2005, 78, 455-461.	1.6	1
108	Structure, magnetic and magnetoresistive properties of La _{0.7} Sr _{0.3} Mn _{1-x} Sn _x O ₃ samples (0 ≤ x ≤ 0.20). Journal of Alloys and Compounds, 2005, 399, 20-26.	2.8	25

#	ARTICLE	IF	CITATIONS
109	Metal oxide gate electrodes for advanced CMOS technology. Annalen Der Physik, 2004, 13, 31-34.	0.9	7
110	Effect of magnetic field orientation on magnetization of (La _{0.7} Sr _{0.3} MnO ₃ /SrTiO ₃) ₁₅ superlattices. Journal of Magnetism and Magnetic Materials, 2004, 272-276, 1260-1262.	1.0	0
111	Magnetism and giant magnetoresistance in La _{0.7} Sr _{0.3} Mn _{1-x} M _x O ₃ (M= Cr, Ti) systems. Physica Status Solidi C: Current Topics in Solid State Physics, 2004, 1, 1649-1654.	0.8	13
112	Ru and RuO ₂ gate electrodes for advanced CMOS technology. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2004, 109, 117-121.	1.7	52
113	Application of Ru-based gate materials for CMOS technology. Materials Science in Semiconductor Processing, 2004, 7, 271-276.	1.9	35
114	Preparation of SrRuO ₃ films for advanced CMOS metal gates. Materials Science in Semiconductor Processing, 2004, 7, 265-269.	1.9	11
115	Growth of lanthanum oxide films for application as a gate dielectric in CMOS technology. Materials Science in Semiconductor Processing, 2004, 7, 231-236.	1.9	33
116	Effect of oxygen post-annealing on the magnetoresistance of highly epitaxial La _{0.7} Ca _{0.3} MnO ₃ thin films. Journal of Magnetism and Magnetic Materials, 2004, 272-276, E1501-E1502.	1.0	1
117	Structural and electrical characterization of magnetoresistive La _{0.7} Ca _{0.3} MnO ₃ thin films. Journal of Magnetism and Magnetic Materials, 2003, 262, 150-153.	1.0	7
118	Defects in (La _{0.7} Sr _{0.3} MnO ₃ /SrTiO ₃) ₁₅ superlattices grown by pulsed injection MOCVD. Journal of Crystal Growth, 2003, 259, 358-366.	0.7	7
119	RBS and ERD study of epitaxial RuO ₂ films deposited on different single crystal substrates. Vacuum, 2003, 70, 313-317.	1.6	2
120	Optical Response of La _{1-x} MnO ₃ /Al ₂ O ₃ Films. Acta Physica Polonica A, 2003, 103, 77-83.	0.2	0
121	Degradation of LaMnO ₃ ^δ surface layer in LaMnO ₃ ^δ /metal interface. Applied Physics Letters, 2002, 81, 859-861.	1.5	26
122	Structure, grain connectivity and pinning of as-deformed commercial MgB ₂ powder in Cu and Fe/Cu sheaths. Superconductor Science and Technology, 2002, 15, 1127-1132.	1.8	37
123	Platinum, Ruthenium and Ruthenium Dioxide Electrodes Deposited by Metal Organic Chemical Vapor Deposition for Oxide Applications. Integrated Ferroelectrics, 2002, 44, 135-142.	0.3	12
124	Low-temperature growth of RuO ₂ films for conductive electrode applications. Materials Science in Semiconductor Processing, 2002, 5, 173-177.	1.9	21
125	Epitaxial growth of low-resistivity RuO ₂ films on -oriented Al ₂ O ₃ substrate. Journal of Crystal Growth, 2002, 235, 377-383.	0.7	16
126	Title is missing!. Journal of Superconductivity and Novel Magnetism, 2002, 15, 579-582.	0.5	4

#	ARTICLE	IF	CITATIONS
127	Growth of magnetoresistant La _{1-x} MnO ₃ films on r-plane cut sapphire. European Physical Journal Special Topics, 2001, 11, Pr3-333-Pr3-339.	0.2	1
128	Photoinduced insulator-metal transition in La _{0.81} MnO ₃ /Al ₂ O ₃ /Nb tunnel junctions. Applied Physics Letters, 2001, 78, 1712-1714.	1.5	14
129	Application of La _{1-x} MnO ₃ giant magnetoresistance sensors for testing of high-TC superconducting tapes. Sensors and Actuators A: Physical, 2001, 91, 21-25.	2.0	2
130	Growth and recrystallization of CeO ₂ thin films deposited on R-plane sapphire by off-axis RF sputtering. Journal of Crystal Growth, 2000, 218, 287-293.	0.7	42
131	Injection MOCVD: ferroelectric thin films and functional oxide superlattices. Surface and Coatings Technology, 2000, 133-134, 191-197.	2.2	31
132	Microstructure-dependent magnetoresistance in La _{1-x} MnO ₃ thin films. Journal of Magnetism and Magnetic Materials, 2000, 211, 67-72.	1.0	14
133	On the problem of overlapping $\tilde{\rho}$ scans measured on thin films deposited on monocystal substrates. Journal of Applied Crystallography, 1999, 32, 736-743.	1.9	2
134	Growth of high crystalline quality thin epitaxial CeO ₂ films on (1102) sapphire. European Physical Journal Special Topics, 1999, 09, Pr8-341-Pr8-347.	0.2	7
135	Effect of crystallinity on the magnetoresistive properties of La _{0.8} MnO ₃ thin films grown by chemical vapor deposition. Applied Physics Letters, 1998, 73, 999-1001.	1.5	57
136	Superconducting films prepared by aerosol metal organic chemical vapour deposition on substrate with buffer layer. Superconductor Science and Technology, 1997, 10, 657-662.	1.8	12
137	Relation between critical current and exponent in Bi(2223)/Ag tapes. Superconductor Science and Technology, 1997, 10, 605-611.	1.8	38
138	HTS thin films by innovative MOCVD processes. Journal of Alloys and Compounds, 1997, 251, 264-269.	2.8	10
139	Growth of YBa ₂ Cu ₃ O ₇ /CeO ₂ /Al ₂ O ₃ heteroepitaxial films by aerosol MOCVD. Journal of Alloys and Compounds, 1997, 251, 284-287.	2.8	3
140	Growth and Structure of Buffer Layers for High Temperature Superconducting Films. Acta Physica Polonica A, 1997, 92, 255-258.	0.2	0
141	TEM characterisation of buffer layers for epitaxial YBa ₂ Cu ₃ O ₇ growth. Physica Status Solidi A, 1995, 150, 371-380.	1.7	3
142	Growth of SrTiO ₃ thin epitaxial films by aerosol MOCVD. Thin Solid Films, 1995, 260, 187-191.	0.8	17
143	Properties of Thin Epitaxial Aerosol MOCVD CeO ₂ Films Grown on (1102) Sapphire. European Physical Journal Special Topics, 1995, 05, C5-533-C5-540.	0.2	3
144	Variable temperature insert for a.c. susceptibility measurements at a.c. field amplitudes up to 0.1 T. Cryogenics, 1994, 34, 837-838.	0.9	7

#	ARTICLE	IF	CITATIONS
145	Influence of heat treatment on the properties of Bi _{1.8} Pb _{0.2} Sr ₂ Ca ₂ Cu ₃ O _x ceramics and Ag-sheathed tapes. <i>Physica C: Superconductivity and Its Applications</i> , 1994, 235-240, 3441-3442.	0.6	1
146	X-ray diffraction analysis of YBCO thin films synthesized by aerosol MOCVD. <i>Physica C: Superconductivity and Its Applications</i> , 1994, 235-240, 657-658.	0.6	0
147	Superconducting properties of YBa ₂ Cu ₃ O ₇ films prepared by aerosol MOCVD. <i>Physica C: Superconductivity and Its Applications</i> , 1994, 235-240, 659-660.	0.6	2
148	Thin epitaxial CeO ₂ films prepared by aerosol MOCVD. <i>Materials Letters</i> , 1994, 21, 377-380.	1.3	10
149	Transport critical current in MOCVD YBa ₂ Cu ₃ O ₇ thin films using a pulse technique. <i>Journal of Alloys and Compounds</i> , 1993, 195, 475-478.	2.8	4
150	Preparation of YBa ₂ Cu ₃ O ₇ films by low pressure MOCVD using liquid solution sources. <i>European Physical Journal Special Topics</i> , 1993, 03, C3-321-C3-328.	0.2	6
151	Preparation and characterization of highly densified YBa ₂ Cu ₃ O _{7-x} Ceramics used for electrochemical oxidation. <i>Zeitschrift Fur Anorganische Und Allgemeine Chemie</i> , 1992, 608, 153-158.	0.6	4
152	MOCVD of YBa ₂ Cu ₃ O _{7-x} thin films using a Ba fluorocarbon-based precursor. <i>Physica C: Superconductivity and Its Applications</i> , 1992, 202, 121-126.	0.6	9
153	Characterization of thin superconducting films prepared by metal-organic chemical vapour deposition. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 1992, 14, 43-45.	1.7	3
154	Preparation and properties of Ba-deficient superconducting thin YBa ₂ Cu ₃ O _x films. <i>Journal of Crystal Growth</i> , 1991, 107, 710-711.	0.7	3
155	Static and dynamic characteristics of Nb ₃ Ge layers for rapid superconducting power switches. <i>Cryogenics</i> , 1991, 31, 590-593.	0.9	2
156	Influence of annealing under oxygen on the chemical and superconducting properties of YBa ₂ Cu ₃ O _x single crystals. <i>Journal of the Less Common Metals</i> , 1990, 164-165, 208-214.	0.9	12
157	Effect of deposition temperature on properties of CVD prepared Nb ₃ Ge superconductor. <i>European Physical Journal D</i> , 1989, 39, 196-206.	0.4	3
158	Critical currents and scaling law in CVD prepared Nb ₃ Ge superconductor alloyed with Al. <i>Cryogenics</i> , 1989, 29, 736-740.	0.9	2
159	AC magnetization of high T _c superconductors at low superimposed DC magnetic fields. <i>Physica C: Superconductivity and Its Applications</i> , 1989, 160, 1-7.	0.6	21
160	Chemical vapour deposition of superconducting Nb ₃ Ge controlled by diffusion in the gas phase. <i>Thin Solid Films</i> , 1987, 150, 311-322.	0.8	7
161	A small Nb ₃ Ge test solenoid. <i>IEEE Transactions on Magnetics</i> , 1987, 23, 577-579.	1.2	0
162	On the relation between T _c measurements and structure inhomogeneity of Nb ₃ Ge superconductor. <i>Acta Physica Academiae Scientiarum Hungaricae</i> , 1982, 53, 419-423.	0.1	4

#	ARTICLE	IF	CITATIONS
163	Development of long Nb ₃ Ge tape with T _c above 20 K. IEEE Transactions on Magnetics, 1981, 17, 2051-2054.	1.2	11
164	Layered Si ₃ N ₄ /(SiALON+TiN) Composites with Self-Diagnostic Ability. , 0, , 559-564.		1
165	Thermal stability of ruthenium MOS gate electrodes. , 0, , .		0
166	Growth and properties of ruthenium based metal gates for pMOS devices. , 0, , .		0